

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

• Features

- AEC-Q101 Qualified
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load Switch

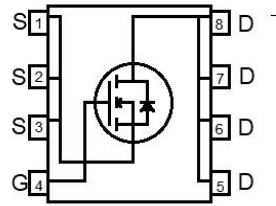
• Ordering Information:

Part NO.	ZMSA100N10M
Marking	100N10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

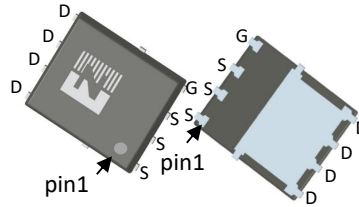
• Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	$V_{DS}$		100	V
Gate-Source Voltage <sup>①</sup>	$V_{GS}$		$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	43	A
	$I_D$	$T_C=75^\circ\text{C}$	34	A
	$I_D$	$T_C=100^\circ\text{C}$	28	A
Pulsed Drain Current	$I_{DM}$	Pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25^\circ\text{C}$ ;	172	A
Total Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	48	W
Total Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	2.5	W
Operating Junction Temperature	$T_J$		-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 to +150	$^\circ\text{C}$
Single Pulse Avalanche Energy	$E_{AS}$	$L=0.1\text{mH}$ , $V_{GS}=10\text{V}$ , $R_g=25\Omega$ ,	97	mJ
		$L=0.5\text{mH}$ , $V_{GS}=10\text{V}$ , $R_g=25\Omega$ ,	184	mJ
ESD Level (HBM)	CLASS 1C			

• Product Summary



$V_{DS} = 100\text{V}$   
 $R_{DS(ON)} = 9\text{m}\Omega$   
 $I_D = 43\text{A}$



DFN3\*3



**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$		-	2.6	°C/W
Thermal resistance, junction-ambient	$R_{thJA}$ <sup>②</sup>		-	50	°C/W
Soldering temperature	Tsold		-	260	°C

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.4	1.7	2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=100V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		9	12	m $\Omega$
		$V_{GS}=4.5V, I_D=16A$		12	15	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_{SD}=10A$		15		S
Diode Forward Voltage	$V_{FSD}$	$V_{GS}=0V, I_{SD}=20A$			1.3	V

**•Dynamic characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	$C_{iss}$	$f=1MHz, V_{DS}=25V$	-	1400	-	pF
Output capacitance	$C_{oss}$		-	630	-	
Reverse transfer capacitance	$C_{rss}$		-	33	-	
Gate Resistance	$R_g$	$f=1MHz$	-	2		$\Omega$
Total gate charge	$Q_g$	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	20	-	nC
Gate - Source charge	$Q_{gs}$		-	3.6	-	
Gate - Drain charge	$Q_{gd}$		-	2.8	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	8	-	ns
Turn-ON Rise time	$t_r$		-	6	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	40	-	ns
Turn-Off Fall time	$t_f$		-	36	-	ns
Reverse Recovery Time	$t_{RR}$	$V_{DD}=20V, di_S/dt=100A/\mu s, I_S=50A$	-	52	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	83	-	nC

Fig.1 Gate-Charge Characteristics

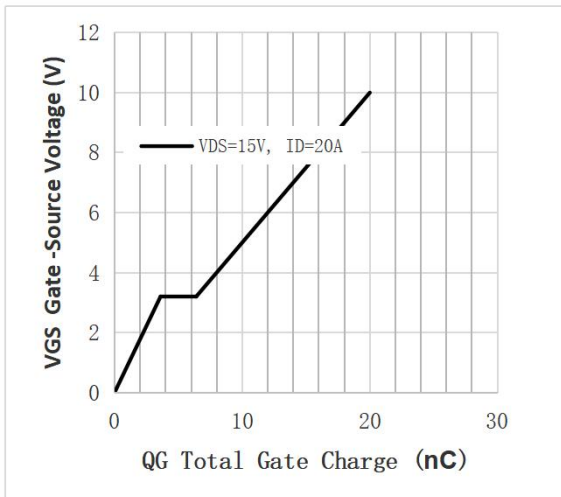


Fig.2 Capacitance Characteristics

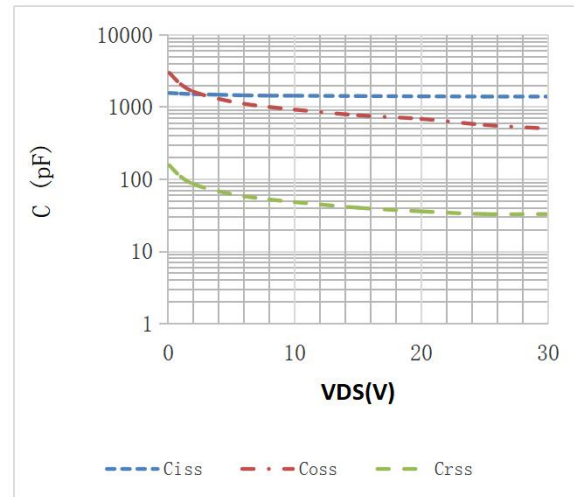


Fig.3 Power Dissipation

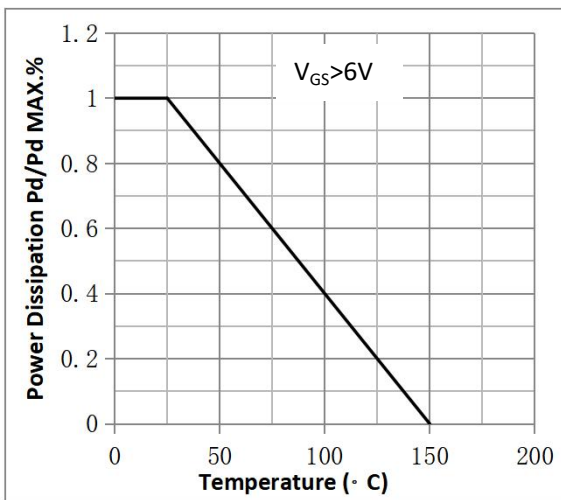


Fig.4 Typical output Characteristics

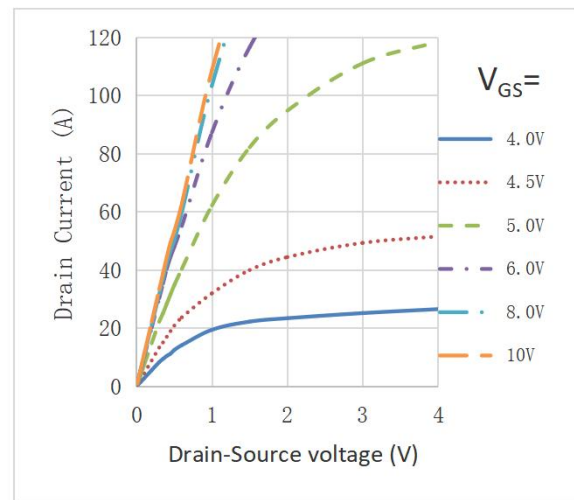


Fig.5 Threshold Voltage V.S Junction Temperature

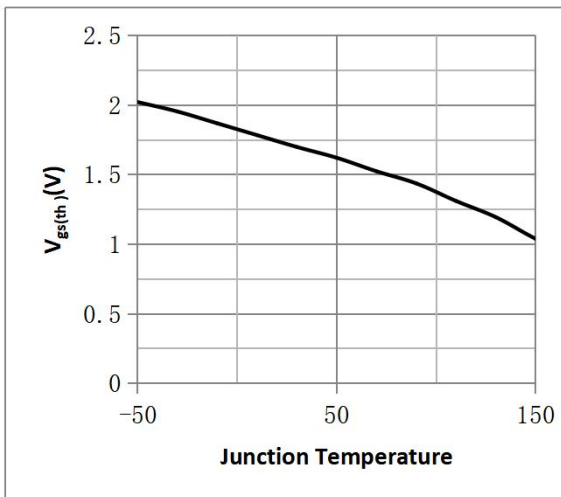


Fig.6 Resistance V.S Drain Current

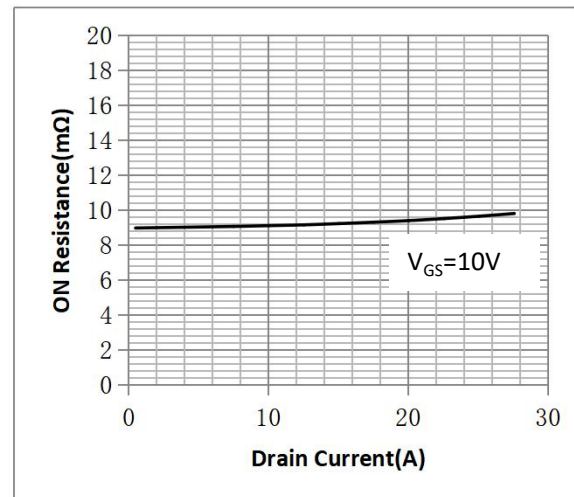


Fig.7 On-Resistance VS Gate Source Voltage

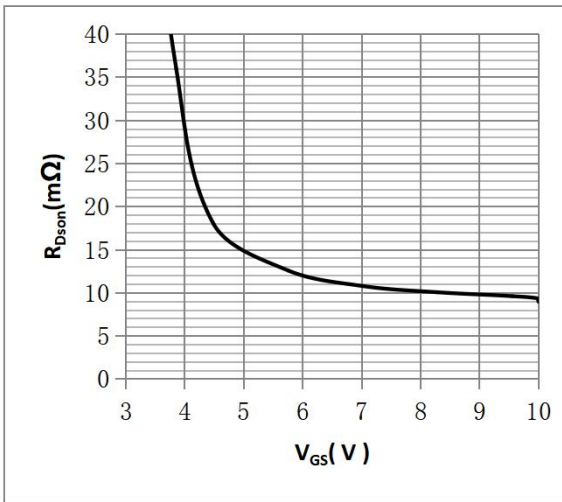


Fig.8 On-Resistance V.S Junction Temperature

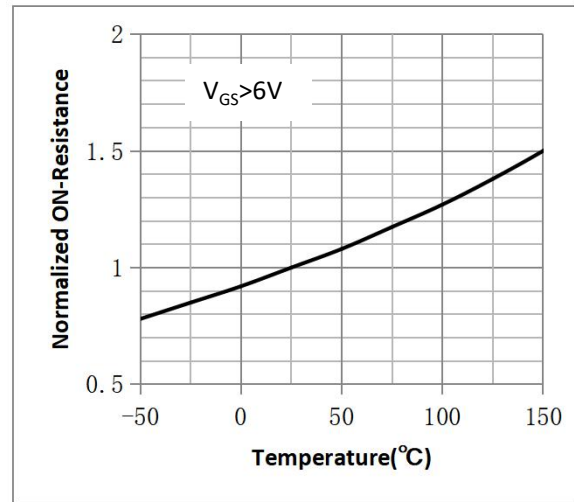


Figure 9. Diode Forward Voltage vs. Current

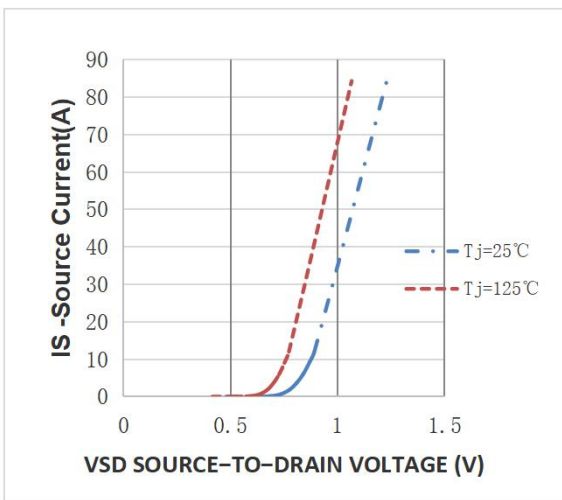


Figure 10. Transfer Characteristics

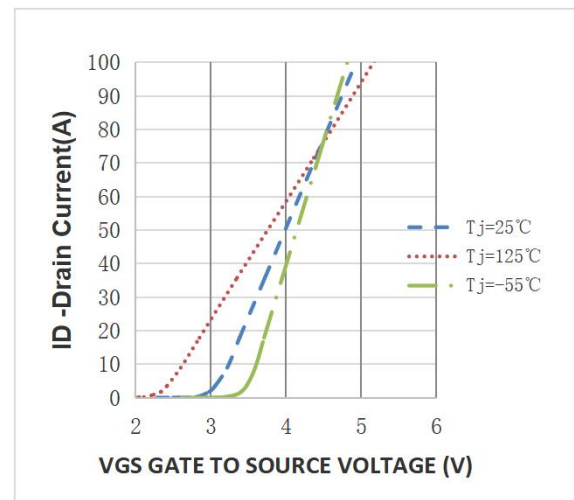


Fig.11 Safe Operating Area

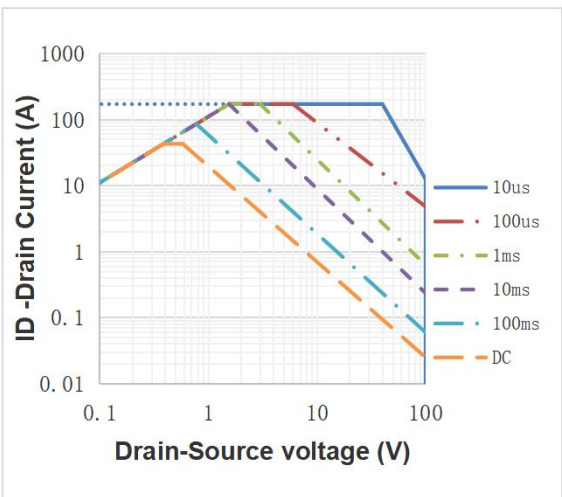
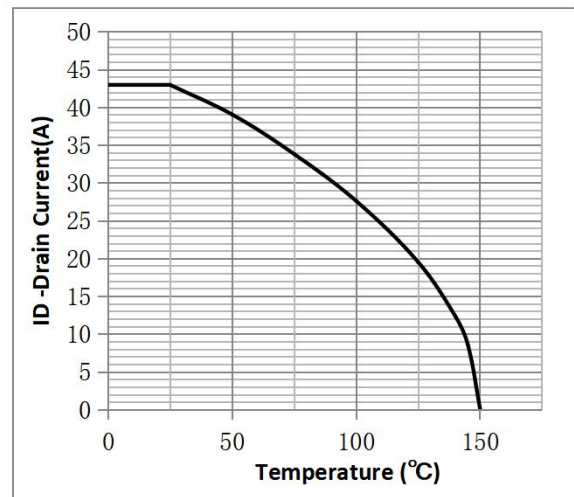
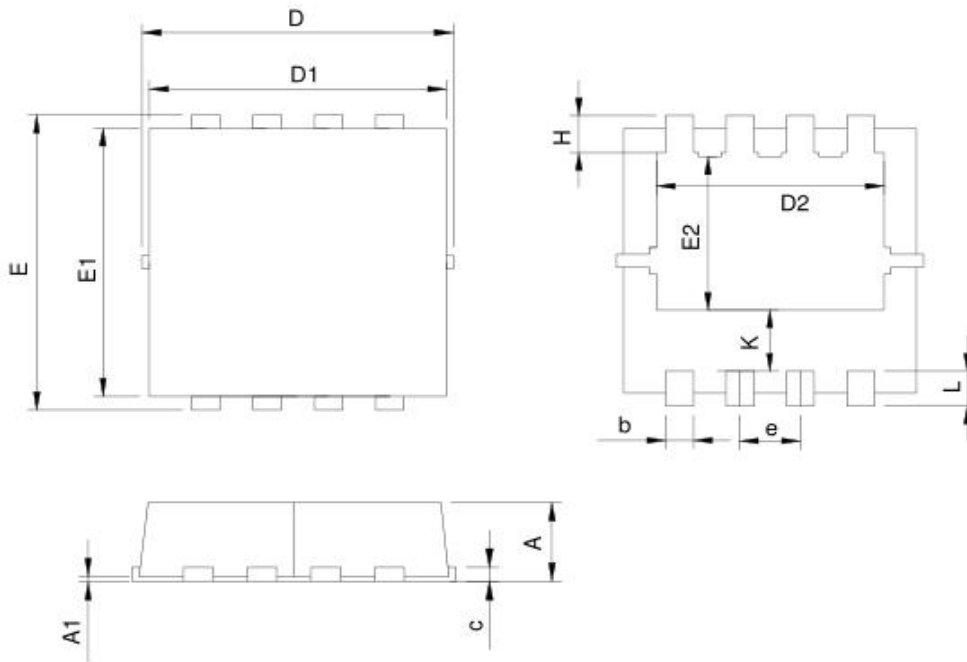


Fig.12 ID vs. Case Temperature<sup>③</sup>

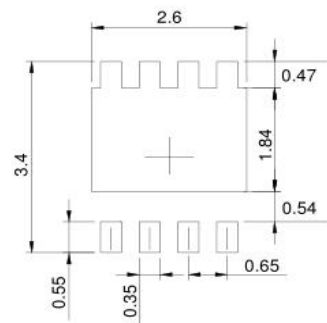


•DFN3\*3 Package Outline



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

**RECOMMENDED LAND PATTERN**



UNIT: mm

**Note:**

- ① Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ , Accumulation time  $\leq 50$  hours; For DC , the following test conditions can be passed:  $V_{GS}=+20V/-10V$ ,  $T_j=150^\circ\text{C}$ ,  $t=1000$  hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature.  $V_{GS}=10V$ .

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Revision History

Version	Date	Change
A	2024.6.26	NEW